

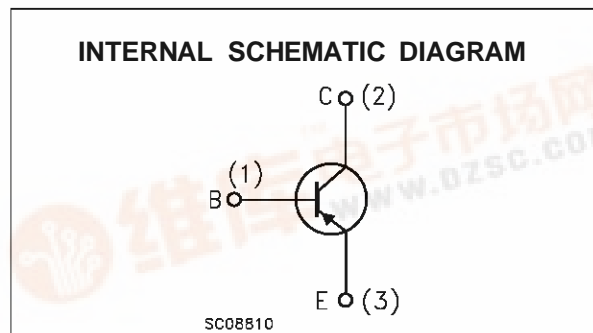


BC857
BC858

SMALL SIGNAL PNP TRANSISTORS

Type	Marking
BC857A	3E
BC857B	3F
BC858A	3J
BC858B	3K

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- VERY LOW NOISE AF AMPLIFIER
- NPN COMPLEMENTS FOR BC857 IS BC847



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BC857	BC858	
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	-50	-30	V
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-50	-30	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-45	-30	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5		V
I_C	Collector Current	-0.1		A
I_{CM}	Collector Peak Current	-0.2		A
I_{BM}	Base Peak Current	-0.2		A
I_{EM}	Emitter Peak Current	-0.2		A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	300		mW
T_{stg}	Storage Temperature	-65 to 150		$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150		$^\circ\text{C}$

BC857/BC858

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	420	°C/W
R_{thj-SR} •	Thermal Resistance Junction-Substrate	Max	330	°C/W

• Mounted on a ceramic substrate area = 10 x 8 x 0.6 mm

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CE} = -30\text{ V}$ $V_{CE} = -30\text{ V}$ $T_{amb} = 150\text{ °C}$			-15 -5	nA μA
$V_{(BR)CES}^*$	Collector-Emitter Breakdown Voltage ($V_{BE} = 0$)	$I_C = -10\text{ }\mu\text{A}$ for BC857 for BC858	-50 -30			V V
$V_{(BR)CBO}^*$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -10\text{ }\mu\text{A}$ for BC857 for BC858	-50 -30			V V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -2\text{ mA}$ for BC857 for BC858	-45 -30			V V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_C = -10\text{ }\mu\text{A}$ for BC857 for BC858	-6 -5			V V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -10\text{ mA}$ $I_B = -0.5\text{ mA}$ $I_C = -100\text{ mA}$ $I_B = -5\text{ mA}$		-0.09 -0.25	-0.3 -0.65	V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = -10\text{ mA}$ $I_B = -0.5\text{ mA}$ $I_C = -100\text{ mA}$ $I_B = -5\text{ mA}$		-0.75 -0.9		V V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = -2\text{ mA}$ $V_{CE} = -5\text{ V}$ $I_C = -10\text{ mA}$ $V_{CE} = -5\text{ V}$	-0.6	-0.66 -0.72	-0.75 -0.82	V V
h_{FE}	DC Current Gain	$I_C = -10\text{ }\mu\text{A}$ $V_{CE} = -5\text{ V}$ for group A for group B $I_C = -2\text{ mA}$ $V_{CE} = -5\text{ V}$ for group A for group B		90 150 110 200	220 450	
f_T	Transition Frequency	$I_C = -10\text{ mA}$ $V_{CE} = -5\text{ V}$ $f = 100\text{ MHz}$		150		MHz
C_{CB}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = -10\text{ V}$ $f = 1\text{ MHz}$			6	pF
NF	Noise Figure	$V_{CE} = -5\text{ V}$ $I_C = -0.2\text{ mA}$ $f = 1\text{ KHz}$ $\Delta f = 200\text{ Hz}$ $R_G = 2\text{ K}\Omega$		2 1.2	10 4	dB dB

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

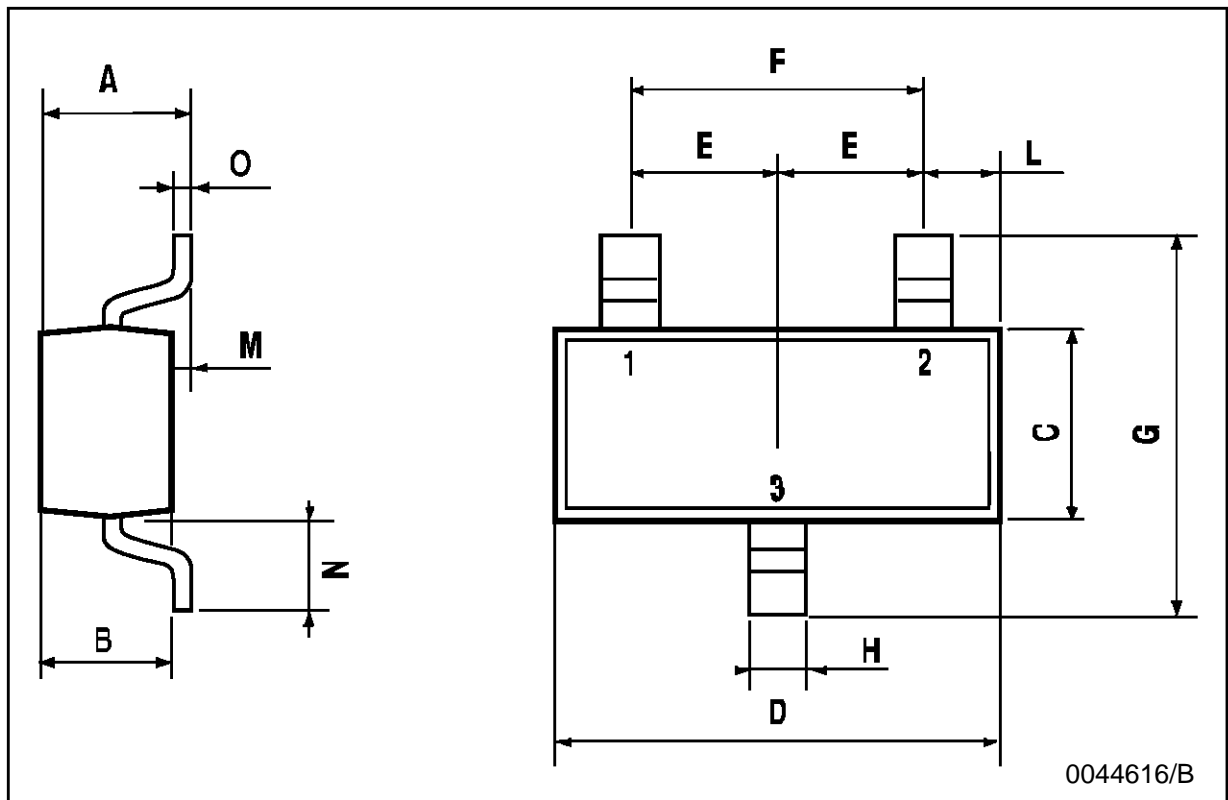
ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
h_{ie}	Input Impedance	$V_{CE} = -5\text{ V}$ $I_C = -2\text{ mA}$ $f = 1\text{ KHz}$ for group A for group B	1.6 3.2	2.7 4.5	4.5 8.5	$\text{K}\Omega$ $\text{K}\Omega$
h_{re}	Reverse Voltage Ratio	$V_{CE} = -5\text{ V}$ $I_C = -2\text{ mA}$ $f = 1\text{ KHz}$ for group A for group B		1.5 2		10^{-4} 10^{-4}
h_{fe}	Small Signal Current Gain	$V_{CE} = -5\text{ V}$ $I_C = -2\text{ mA}$ $f = 1\text{ KHz}$ for group A for group B		220 330		
h_{oe}	Output Admittance	$V_{CE} = -5\text{ V}$ $I_C = -2\text{ mA}$ $f = 1\text{ KHz}$ for group A for group B		18 30	30 60	μs μs

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



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